

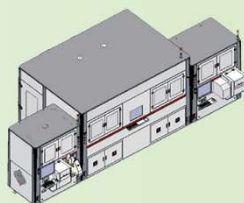
NATS-Series

オートモーティブデバイスの前工程から後工程まで各種検査システムをラインナップ
Power semiconductor Front-End / Back-End Test System

Wafer

Die / Chip

NATS-1302 / 1303



KGD AC/DC Test System

NATS-1302 : DC/AC Test
Multiple Temp Control ~200°C
3 Stage + Liner Handler Type
UPH 1000 chips

NATS-1303 : DC/AC Test
Multiple Temp Control ~200°C
4 Stage + Index Handler Type
UPH 2000 chips

ウェハーからダイ、チップレベルに対応する
各種ハンドラーを取り揃え、高スループット
Applied to Wafer / Die / Chip level and high-through put

DBC / AMB

NATS-1202



DBC/AMB Test System

最大3000A / 1500V

ワイヤボンディング前後のDBCおよびAMBの静的/動的機能検査に対応
Static and dynamic functionality tester for DBC and AMB before/after wire bonding

AQG324 試験規格 Silicon Carbide FET 対応機種

AQG324 test standard Silicon carbide FET compatible model

Module

NATS-8151/ 8152



Dynamic HTRB HTGB Tester

高温逆バイアス DHTRB / 高温ゲートバイアス DHTGB

広い周波数範囲と柔軟なパラメータ設定に対応するAC/DCテストが可能
Wide range frequency / Flexible setting AC/DC test available

NATS-8153



Dynamic H3TRB Tester

高温高湿逆バイアス Dyn H³TRB

複数レイヤーを個別 / 同時実行を可能とし最小動作単位は1レイヤーから設定可能
Individual / simultaneous execution setting of multiple layers,
and the Minimum operation unit can be set from 1 layer

NATS-8140



Continuous Power Characterizer

連続出力特性検査 | Continuous Power Characterize

CMTI : Max200kV/μs
Output Phase Current : 800Arms
Frequency : 1000Hz

NATS-1302/1303

Specification	NATS-1302	NATS-1303-Turret	NATS-1303-Index
Fixture	N2 Purge Fixture	Compressed Dry Air Fixture	Compressed Dry Air Fixture
Handler Type / Num of Test Stage	Linear / 3	Turrent Table / 4	Index Table / 4
Input	6,8,12-inch wafer frame	4-inch tray, 6,8,12-inch wafer frame	4-inch tray, 6,8,12-inch wafer frame
Output	Wafer frame, tray	Wafer frame, Tray, Tape, Tube	Wafer frame , Tray, Tape, Tube
Temp control 25~200℃	Room Temp, High Temp($\leq 200^{\circ}\text{C}$)	Room Temp, High Temp($\leq 200^{\circ}\text{C}$)	Multiple Temp($25^{\circ}\text{C}\sim 200^{\circ}\text{C}$)
UPH	≤ 1000	≥ 2000	≥ 2000
Tester	AC, DC	AC,DC	AC,DC
High Current AC	3000A	1200A	1200A
Visual Inspection	Optional	N.A.	Optional

AC Test Characteristics	
Model	R-723x
Test condition	Vcc: 50V~3000V Ids: 10A~ 1200A (*1) , Isc: 10A~ 3,000A (*1)
Gate Driver	Vgs(on) 10V~25V, Vgs(off) -15V~0V RG 0~31.5ohm (0.5ohm step), (+2 optional resistors) 2ch, Tw=0.1us~999us
Coil	15uH, 25uH, 50uH, 100uH, 200uH (*1)
Test item	Double pulse, Diode, Multi pulse, SCSOA, EAS(*2), Contact check
Oscilloscope	8ch, 1GHz, 3.125Gsps, 12bit
characteristic	Tdon, Tr, Ton, Eon, di/dt, dv/dt, Icoff, Vcepeak, Icpeak, Tdoff, Tf, Toff, Eoff trr, Err, Qrr, Vccr, Vrrpeak, IFM, IRM, Prec, di/dt(Rec), dv/dt(Rec), tsc, Esc, Pmax, Isc
Over Current protection	Turn-off time < 0.5us

*1 Depends on requirement specification
*2 Additional Options

DC Test Characteristics	
Model	R-722x (TBD)
Test condition	Vds: 1V ~ 3000V (*1) Id: 20A ~ 1000A (*1) Vgs: -15V~ +25V
DC parametric	Vds 3000V (0.02A) 1500V (0.12A)
	Id 1000A (0.5ms) 250A (2ms)
	Vgs +/- 50V (0.1A) +/- 20V (1.0A)
Characteristic	V(BR)dss, Idss, Igss, Vgs(th), Vds(on), Rds(on), Vsd, Contact check, Ciss(*2), Coss(*2), Crss(*2) , Qg(*2)

*1 Depends on requirement specification
*2 Additional Options

NATS-1202

Specification	NATS-1202	
Handler Type / Num of Test Station	AC+DC Station / 2	In-Line FT / 4
Input	Tray Stacker	Tray Stacker
Output	Tray Stacker	Tray Stacker
UPH	≤600	≤360
Tester	AC, DC	AC, DC

DC Static Tester Specification			
Items	Range	Minimum resolution	Accuracy
Ice/Ids setting	0~800A(20Vmax)	1A	±0.5%±100mA
Vge/Vgs setting	-20.0V~+20.0V	0.1V	±0.2%±0.1V
Vce/Vds setting	~1300.0V	0.1V	±0.1%±1V
Vge/Vgs setting	-100.0V~+100.0V	0.1V	±0.1%±1V
Force time	0.01s~9.99s	0.01s	-
Vge/Vds, Vf/Vrec, measurement	0.0V~10.0000V	0.1mV	±0.1%±1mV
Ic/Ids measurement	~1.0000uA	0.1nA	±0.1%±2nA
	~10.000uA	1nA	±0.1%±10nA
	~100.00uA	10nA	±0.1%±100nA
	~1.0000mA	100nA	±0.1%±1uA
	~10.000mA	1uA	±0.1%±10uA
Ige/gs measurement	~0.10000uA	0.01nA	±0.1%±1nA
	~1.0000uA	0.1nA	±0.1%±2nA
	~10.000uA	1nA	±0.1%±10nA
	~100.00uA	10nA	±0.1%±100nA
	~1000.0uA	100nA	±0.1%±1uA

Isolation Tester Specification			
Leakage current between terminals and base-plate			
Items	Range	Minimum resolution	Accuracy
Force voltage	0.5kVrms~5.0kVrms	10V	-
Current limit	10mA~99mA	1mA	-
Current measurement	0.01mA~99.9mA	10uA	±3%±30uA
Force time	0.1s~99.9s	0.1s	-
Isolation resistance between main/aux terminals and thermistor/base-plate			
Items	Range	Minimum resolution	Accuracy
Force voltage	50V~1200V	50V	-
Short-circuit current	10mA	-	-
Insulation resistance	0.1MΩ~10GΩ	-	±20%
Force time	0.1s~99.9s	0.1s	-

Dynamic Tester Specification			
AC Test Data			
Items	Range	Minimum resolution	Accuracy
VCC voltage	1.0V~1500.0V	0.1V	±0.5%±1V
VGE voltage	+10.0V~+20.0V,+25.0V -15.0V~0.0V	0.1V	±0.2%±0.1V
IC, IF	Up to 1600A		
Rg resistance	1Ω~255Ω	1Ω	±0.7
Pulse on/off time	1.0us~999.9us	0.1us	±0.2%±0.1us
Number of pulses	1~32	-	-
Load inductance (L)	25uH, 50uH, 75uH, 100uH, 200uH	-	-
Measurement items	Range	Minimum resolution	Accuracy
VGE	±150V	0.02V	±1% of F.S
VCE, VR	±1500V	0.25V	±1% of F.S
IC, IF	±6000A	0.5A	±1% of F.S

NATS-8151/8152

	NATS-8151 DHTRB	NATS-8152 DHTGB
Topology	Heat Plate Type	Heat Plate Type
Discrete	Passive/Active 4-layer per cabinet Max 20 per layer Max 100	4-layer per cabinet Max 20 per layer Max 100
Half Bridge	Passive 4-layer per load Max 6 per layer Max 24 Active Max 12 per layer Max 48	4 -load per cabinet Max 12 per layer Max 48
6-in-1	Passive 4-layer per cabinet Max 2 per layer Max 8 Active Max 6 per layer Max 24	4-layer per cabinet Max 6 per layer Max 24

NATS-8151 DHTRB / DRB	NATS-8152 DHTGB / DGS
Temperature: Room temperature-200°C	Temperature: Room temperature-200°C
Drain-source voltage: 0-2000V adjustable, ≤0.3, duty cycle 0-1 adjustable	Gate Drive: ±30V adjustable, ≤0.1V, duty cycle 0-1 adjustable
Switch Frequency: 0-500kHz for discrete, 0-50kHz for module	Switch Frequency: 0-500kHz for discrete, 0-100kHz for module
Drain-source leakage current range 0A-100mA	Gate-source leakage current range: 0A-100mA
100nA, ±1%+10nA	10nA, ±0.100%+50pA
1uA, ±1%+20nA	100nA, ±0.060%+100pA
10uA, ±1%+200nA	1uA, ±0.025%+300pA
1mA, ±1%+2uA	10uA, ±0.025%+700pA
100mA, ±1%+200uA	100uA, ±0.025%+6nA
	1mA, ±0.020%+60nA
	10mA, ±0.020%+600nA
	100mA, ±0.025%+6uA
dV/dt: Discrete > 50V/ns (no overshoot) Module > 30V/ns (no overshoot)	dV/dt: Discrete > 1V/ns (no overshoot) Module up to 1V/ns
Structure	Layers: 1~5 Standalone Dedicated to DHTGB or DHTRB
Function	DHTGB/DHTRB for Discrete & Module
Capacity	Discrete (TO247-3/4 Compatible) DCM HPD DHTGB: 4 layers, 20pcs/layer, max 80 DHTGB: 4 layers, 12pcs/layer, max 48 DHTGB: 4 layers, 6pcs/layer, max 24 DHTRB:(active) 4 layers, 20pcs/layer, max 80 DHTRB:(active) 4 layers, 12pcs/layer, max 48 DHTRB:(active) 4 layers, 6pcs/layer, max 24 DHTRB:(passive) 4 layers, 20pcs/layer, max 80 DHTRB:(passive) 4 layers, 6pcs/layer, max 24 DHTRB:(passive) 4 layers, 2pcs/layer, max 8

NATS-8151 DHTRB			NATS-8152 DHTGB		
Parameters			Parameters		
High dV/dt	TO247-3&TO247-4	>80V/ns@Less than15%overshoot	High dV/dt	TO247-3&TO247-4	> 1V/ns@no overshoot
	Half-bridge	>50V/ns@Less than15% overshoot		Half-bridge	up to1V/ns@no overshoot
	HPD	>50V/ns@Less than15% overshoot		HPD	up to1V/ns@no overshoot
	Adjustable wide range frequency	TO247-3&TO247-4	0-500kHz	Adjustable wide range frequency	TO247-3&TO247-4
Half-bridge		0-50kHz	Half-bridge		0-100kHz
HPD		0-50kHz	HPD		0-100kHz
Adjustable duty cycle	TO247-3&TO247-4	0-100%	Adjustable duty cycle	TO247-3&TO247-4	0-100%
	Half-bridge	0-100%		Half-bridge	0-100%
	HPD	0-100%		HPD	0-100%
Performance			Performance		
Temperature	Normal - 200℃ (the temperature a group of 10 DUTs can be individually controlled)		Temperature	Normal - 200℃ (the temperature a group of 10 DUTs can be individually controlled)	
Accuracy	Accuracy ≤±3℃		Accuracy	Accuracy ≤±3℃	
Gate drive	±35V adjustable		Gate drive	±35V adjustable	
Gate drive accuracy	Accuracy ≤0.1V		Gate drive accuracy	Accuracy ≤0.1V	
Duty cycle	0-100% adjustable		Duty cycle	0-100% adjustable	
	0-500kHz adjustable			0-500kHz adjustable	
	Discrete			Discrete	
Switch frequency	0-100kHz adjustable		Switch frequency	0-100kHz adjustable	
	Modules			Modules	
Range of gate leakage current	0-100mA		Range of gate leakage current	0-100mA	
Accuracy of gate leakage current	10nA		Accuracy of gate leakage current	10nA	
	±0.100%+50pA			±0.100%+50pA	
	100nA			100nA	
	±0.060%+100pA			±0.060%+100pA	
	1uA			1uA	
	±0.025%+300pA			±0.025%+300pA	
Accuracy of drain leakage current	10uA		Accuracy of drain leakage current	10uA	
	±0.025%+700pA			±0.025%+700pA	
	100uA			100uA	
	±0.025%+6nA			±0.025%+6nA	
	1mA			1mA	
	±0.020%+60nA			±0.020%+60nA	
dVds/dt	10mA		dVgs/dt	10mA	
	± 0.020%+600nA			± 0.020%+600nA	
	100mA			100mA	
	±0.025%+6uA			±0.025%+6uA	
	> 1V/ns(No overshoot)			> 1V/ns(No overshoot)	
	Discrete			Discrete	
	up to1V/ns			up to1V/ns	
	Modules			Modules	

NATS-8153

NATS-8153 DH3TRB		
Topology	Chamber Type (1000L)	
Discrete	Passive 10-layer per cabinet Max 24 per layer Max 240	Active 8-layer per cabinet Max 10 per layer Max 80
Half Bridge	Passive 10-layer per cabinet Max 6 per layer Max 60	Active 4-layer per cabinet Max 6 per layer Max 24
6-in-1	Passive 10-layer per cabinet Max 2 per layer Max 20	Active 4-layer per cabinet Max 2 per layer Max 8

NATS-8153 DH3TRB			
Temperature: -20-125°C, <±5%, fluctuation ≤0.5°C			
Drain-source Voltage: 0-2000V adjustable, ≤0.3%, duty cycle 0-1 adjustable			
Stress Frequency: Discrete(active:0-50kHz passive:0-25kHz) Module(active & passive 0-25kHz)			
Stress duty cycle: 0-100% adjustable			
Drain-source Leakage Current Measure Range: 0nA-100mA, 100nA±(1%+10nA), 1uA±(1%+20nA), 10uA±(1%+200nA), 1mA±(1%+2uA), 100mA±(1%+200uA)			
dV/dt: Discrete(active:>50V/ns while 0.5Vdsmax, Vds<80%Vdsmax Passive:>30V/ns(less than15%overshoot) Module(active & passive >30V/ns less than15%overshoot)			
Heating Method	Incubator Heating		
Function	DH3TRB for Discrete & Module		
Capacity	Discrete (TO247-3/4 Compatible)	DCM	HPD
	Passive: 10 layers, 24/layer, max 240 Active: 8 layers, 10/layer, meets AQG-324 qualifications	Passive: 10 layers, 6/layer, max 60 Active: 4 layers, 6/layer, meets AQG-324 qualifications	Passive: 10 layers, 2/layer, max 20 Active: 4 layers, 2/layer, meets AQG-324 qualifications

NATS-8153 DH3TRB		
Parameters		
High dV/dt	TO247-3&TO247-4	> 30V/ns(less than15%overshoot) > 50V/ns(0.5Vdsmax, Vds<80%Vdsmax)
	Half-bridge	> 30V/ns(less than15%overshoot) > 50V/ns(0.5Vdsmax, Vds<80%Vdsmax)
	HPD	> 30V/ns(less than15%overshoot) > 50V/ns(0.5Vdsmax, Vds<80%Vdsmax)
Adjustable wide range frequency	TO247-3&TO247-4	0-500kHz
	Half-bridge	0-50kHz
	HPD	0-50kHz
Adjustable duty cycle	TO247-3&TO247-4	0-100%
	Half-bridge	0-100%
	HPD	0-100%
Performance		
Temperature	Temperature: -20°C-125°C	
Temperature deviation	Deviation <±2.0°C	
Temperature fluctuation	Fluctuation ≤0.5°C	
Humidity	10%~98%	
Humidity fluctuation	Fluctuation ≤±3%RH	
Drain voltage	0-2000V adjustable	
Drain voltage accuracy	≤0.3%	
Duty cycle	0-100% adjustable	
Switch frequency	0-500kHz adjustable	Discrete
	0-50kHz adjustable	Module
Range of drain leakage current	0-100mA	
Accuracy of drain leakage current	100nA	±1%+10nA
	1uA	±1%+20nA
	1mA	±1%+2uA
	100mA	±1%+200uA
dVds/dt	> 30V/ns(less than15%overshoot)	
	> 50V/ns(0.5Vdsmax, Vds<80%Vdsmax)	

NATS-8140

NATS-8140			
Type	Index	Parameter	Notes
High voltage power supply	Input voltage	380V±15%	
	Frequency	50Hz±3Hz	
	Output voltage	0~1500V	Accuracy: 1%
Load inductance	Inductance	20μH	
	Working current	3Arms~800Arms	
	Insulation level	Class H	
	Dielectric strength	Cored winding: 3000V AC/50Hz/5mA/10s No flashover breakdown	
	Noise	≤65dB	
	Heat dissipation	Air cooling	
Water chiller	Temperature range	5℃~85℃	Accuracy±0.5℃
	Flow range	5~20L/min	±0.5L/min
	Coolant composition	50% ethylene glycol, 50% water	(Car use, with preservatives and water scale proof)